

AMENDMENTS TO THE CLAIMS

A listing of the claims presented in this patent application appears below. This listing replaces all prior versions and listing of claims in this patent application.

Claim 1 (previously amended): A method for manufacturing a SiC device, using selective oxidization of silicon, ascribable to the difference between an oxidation rate for SiC and the oxidation rate for silicon, without using a silicon nitride film as an oxidation protection mask, the method comprising:

depositing a silicon film above a SiC substrate;

delineating the silicon film into a required pattern so as to expose a part of a surface of the SiC substrate; and

selectively oxidizing the delineated silicon film so as to grow a localized thermal oxide film in the required pattern above the SiC substrate by exposing simultaneously the part of the surface of the SiC substrate and all of the delineated silicon film to a water rich ambient.

Claim 2 (original): The method of claim 1, wherein H_2O partial pressure in the water rich ambient is selected such that oxidation rate for the silicon film is larger than that for the SiC substrate.

Claim 3 (original): The method of claim 2, wherein the H_2O partial pressure in the water rich ambient is kept more than 0.95.

Claim 4 (original): The method of claim 1, wherein said silicon film is delineated into a pattern for an element isolation region.

Claim 5 (previously amended): A method for manufacturing a SiC device, comprising:
depositing a silicon film above a SiC substrate;
delineating the silicon film into required pattern;
annealing the SiC substrate in a water rich ambient to selectively grow a localized thermal oxide film above the SiC substrate;

forming a trench at the surface of the SiC substrate, before depositing said silicon film, wherein the silicon film is delineated such that the silicon film buries the trench, and the silicon film buried in the trench is selectively oxidized in the water rich ambient.

Claim 6 (original): The method of claim 1, further comprising forming a blanket silicon oxide film at the surface of the SiC substrate in an oxygen added ambient, before depositing said silicon film so that said silicon film can deposit on the blanket silicon oxide film.

Claim 7 (original): The method of claim 6, wherein the H₂O partial pressure in the oxygen added ambient is kept less than 0.95.

Claim 8 (original): The method of claim 6, further comprising selectively removing said blanket silicon oxide film using said silicon film as an etching mask so as to expose a part of the surface of the SiC substrate, before said silicon film is selectively oxidized in the water rich ambient,

Claim 9 (previously amended): A method for manufacturing a SiC device, comprising:
forming a blanket silicon oxide film at the surface of the SiC substrate in an oxygen added ambient;

depositing a silicon film on the blanket silicon oxide film;

delineating the silicon film into a required pattern;

selectively removing the blanket silicon oxide film using the silicon film as an etching mask so as to expose a part of the surface of the SiC substrate;

annealing the SiC substrate in a water rich ambient to selectively grow a localized thermal oxide film above the SiC substrate; and

forming a thin silicon oxide film at the exposed part of the surface of the SiC substrate in the oxygen added ambient after selectively growing said localized thermal oxide film,

wherein the oxygen added ambient and the water rich ambient are successively achieved in a same reaction tube so as not to expose the surface of the SiC substrate to an air outside of the reaction tube.

Claim 10 (original): The method of claim 1, wherein said water rich ambient is achieved by directly introducing ultra pure water in a reaction tube for oxidation.

Claim 11 (previously amended): A method for manufacturing a SiC device, comprising:

forming a blanket silicon oxide film at the surface of the SiC substrate in an oxygen added ambient;

depositing a silicon film on the blanket silicon oxide film;

delineating the silicon film into a required pattern;

selectively removing the blanket silicon oxide film using the silicon film as an etching mask so as to expose a part of the surface of the SiC substrate;

annealing the SiC substrate in a water rich ambient to selectively grow a localized thermal oxide film above the SiC substrate;

forming a gate oxide film at the exposed part of the surface of the SiC substrate in the oxygen added ambient; and

annealing said gate oxide film in the water rich ambient at substrate temperature lower than the substrate temperature at which the gate oxide film is formed.

Claim 12 (original): The method of claim 8, further comprising:

depositing another silicon film at the exposed part of the surface of the SiC substrate;

annealing the SiC substrate in the water rich ambient to grow a gate oxide film at the exposed part of the surface of the SiC substrate; and

annealing said gate oxide film in the water rich ambient at substrate temperature equal to or lower than the substrate temperature at which the gate oxide film is grown.

Claims 13-20 (canceled).